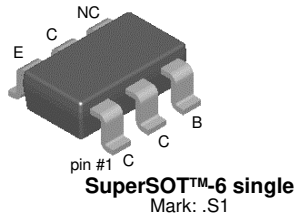


# FMBS549 PNP Low Saturation Transistor

## Features

- This device is designed with high current gain and low saturation voltage with collector currents up to 2A continuous.
- Sourced from process PB.



## Absolute Maximum Ratings \* $T_a = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Unit
$V_{CEO}$	Collector-Emitter Voltage	-30	V
$V_{CBO}$	Collector-Base Voltage	-35	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current - Continuous - Peak Pulse Current	-1 -2	A A
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	- 55 ~ 150	$^\circ\text{C}$

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

## Thermal Characteristics \*

Symbol	Parameter	Value	Unit
$P_D$	Total Device Dissipation, by $R_{\theta JA}$	700	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	180	$^\circ\text{C}/\text{W}$

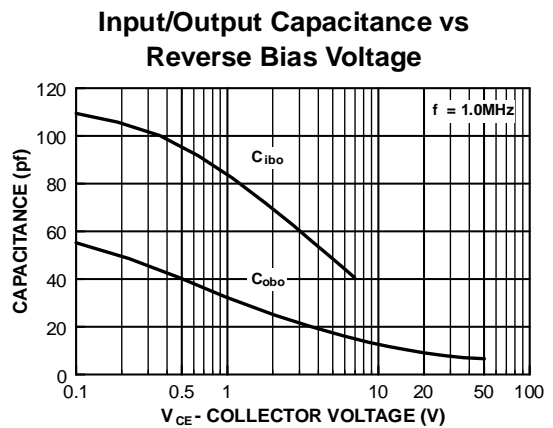
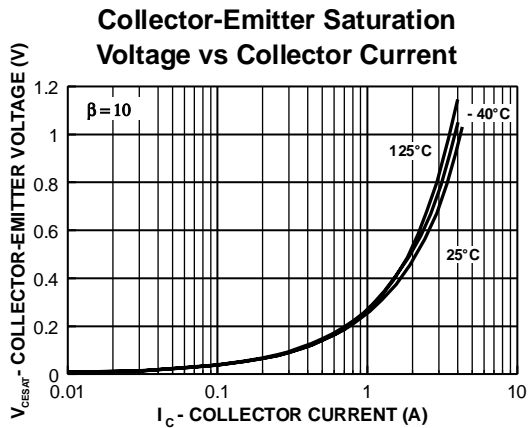
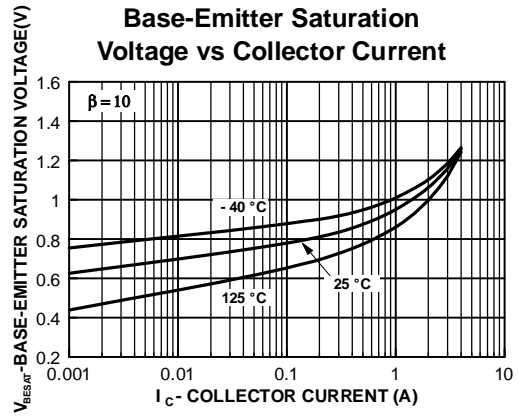
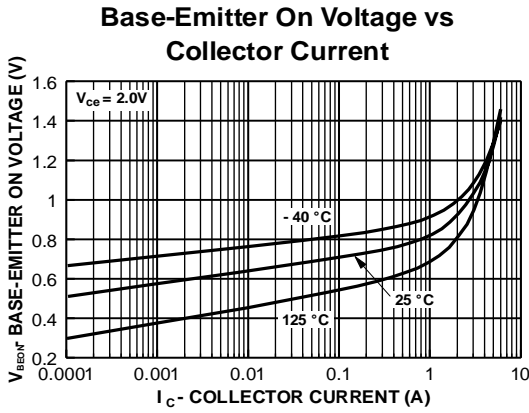
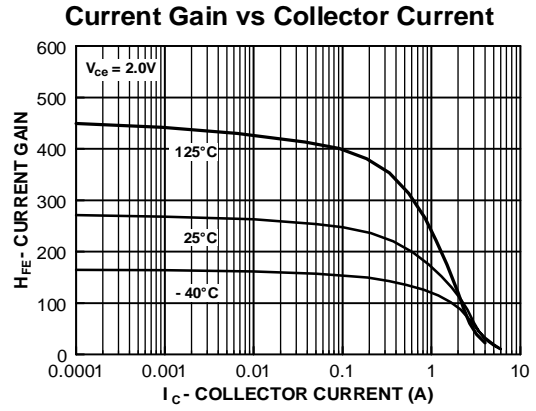
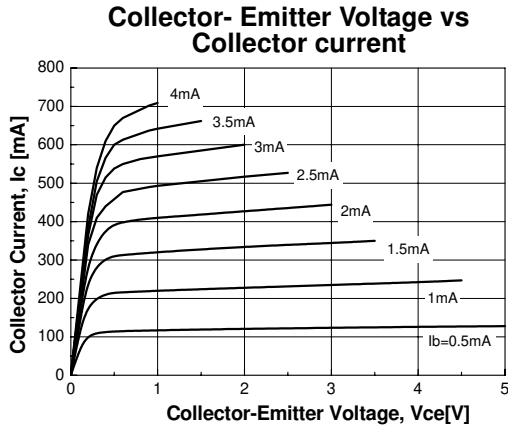
\* Device mounted on a 1 in<sup>2</sup> pad of 2 oz copper.

**Electrical Characteristics\***  $T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Conditions	Min.	Max.	Units
<b>Off Characteristics</b>					
$BV_{CEO}$	Collector-Emitter Breakdown Voltage *	$I_C = -10\text{mA}, I_B = 0$	-30		V
$BV_{CBO}$	Collector-Base Breakdown Voltage	$I_C = -100\mu\text{A}, I_E = 0$	-35		V
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = -100\mu\text{A}, I_C = 0$	-5.0		V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -30\text{V}, I_E = 0$ $V_{CB} = -30\text{V}, I_E = 0, T_a = 100^\circ\text{C}$		-100 -10	nA $\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -4.0\text{V}, I_C = 0$		-100	nA
<b>On Characteristics *</b>					
$h_{FE}$	DC Current Gain	$V_{CE} = -2.0\text{V}, I_C = -50\text{mA}$ $V_{CE} = -2.0\text{V}, I_C = -500\text{mA}$ $V_{CE} = -2.0\text{V}, I_C = -1\text{A}$ $V_{CE} = -2.0\text{V}, I_C = -2\text{A}$ $V_{CE} = -0.8\text{V}, I_C = -500\text{mA}$	70 100 80 40 100	300	
$V_{CE}(\text{sat})$	Collector-Emitter Saturation Voltage	$I_C = -250\text{mA}, I_B = -25\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$ $I_C = -1\text{A}, I_B = -100\text{mA}$ $I_C = -2\text{A}, I_B = -200\text{mA}$		-200 -350 -500 -750	mV mV mV mV
$V_{BE}(\text{sat})$	Base-Emitter Saturation Voltage	$I_C = -1\text{A}, I_B = -100\text{mA}$		-1.25	V
$V_{BE}(\text{on})$	Base-Emitter On Voltage	$I_C = -1\text{A}, V_{CE} = -2.0\text{V}$		-1.0	V
<b>Small Signal Characteristics</b>					
$f_T$	Current Gain Bandwidth Product	$I_C = -100\text{mA}, V_{CE} = -5\text{V},$ $f = 100\text{MHz}$	100		MHz
$C_{ob}$	Output Capacitance	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		25	pF

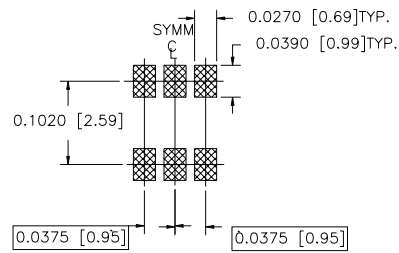
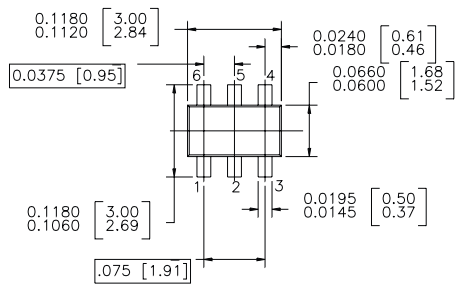
\* DC Item are tested by Pulse Test: Pulse Width $\leq$ 300us, Duty Cycle $\leq$ 2%

## Typical Characteristics



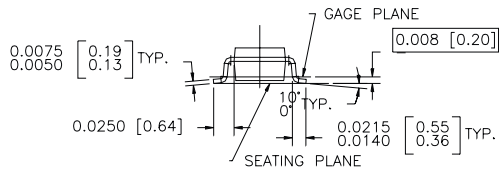
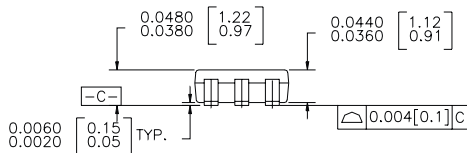
# Package Dimensions

## SuperSOT™-6



LAND PATTERN RECOMMENDATION

CONTROLLING DIMENSION IS INCH  
VALUES IN [ ] ARE MILLIMETERS



SUPER SOT 6 LEADS

NOTES : UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH : 150 MICRINCHES 93.81 MICROMETERS)  
MINIMUM TIN / LEAD (SOLDER) ON COPPER.

2.0 NO JEDEC REGISTRATION AS OF JULY 1996

Dimensions in Millimeters

**TRADEMARKS**

The following are registered and unregistered trademarks Fairchild Semiconductor owns or is authorized to use and is not intended to be an exhaustive list of all such trademarks.

ACE <sup>x</sup> <sup>TM</sup>	FACT Quiet Series <sup>TM</sup>	OCX <sup>TM</sup>	SILENT SWITCHER <sup>®</sup>	UltraFET <sup>®</sup>
ActiveArray <sup>TM</sup>	GlobalOptoisolator <sup>TM</sup>	OCXPro <sup>TM</sup>	SMART START <sup>TM</sup>	UniFET <sup>TM</sup>
Bottomless <sup>TM</sup>	GTO <sup>TM</sup>	OPTOLOGIC <sup>®</sup>	SPM <sup>TM</sup>	VCX <sup>TM</sup>
Build it Now <sup>TM</sup>	HiSeC <sup>TM</sup>	OPTOPLANAR <sup>TM</sup>	Stealth <sup>TM</sup>	Wire <sup>TM</sup>
CoolFET <sup>TM</sup>	I <sup>2</sup> C <sup>TM</sup>	PACMAN <sup>TM</sup>	SuperFET <sup>TM</sup>	
CROSSVOLT <sup>TM</sup>	i-Lo <sup>TM</sup>	POP <sup>TM</sup>	SuperSOT <sup>TM</sup> -3	
DOME <sup>TM</sup>	ImpliedDisconnect <sup>TM</sup>	Power247 <sup>TM</sup>	SuperSOT <sup>TM</sup> -6	
EcoSPARK <sup>TM</sup>	IntelliMAX <sup>TM</sup>	PowerEdge <sup>TM</sup>	SuperSOT <sup>TM</sup> -8	
E <sup>2</sup> C <sup>MOS</sup> <sup>TM</sup>	ISOPLANAR <sup>TM</sup>	PowerSaver <sup>TM</sup>	SyncFET <sup>TM</sup>	
EnSigna <sup>TM</sup>	LittleFET <sup>TM</sup>	PowerTrench <sup>®</sup>	TCM <sup>TM</sup>	
FACT <sup>TM</sup>	MICROCOUPLER <sup>TM</sup>	QFET <sup>®</sup>	TinyBoost <sup>TM</sup>	
FAST <sup>®</sup>	MicroFET <sup>TM</sup>	QS <sup>TM</sup>	TinyBuck <sup>TM</sup>	
FAST <sup>r</sup> <sup>TM</sup>	MicroPak <sup>TM</sup>	QT Optoelectronics <sup>TM</sup>	TinyPWM <sup>TM</sup>	
FPS <sup>TM</sup>	MICROWIRE <sup>TM</sup>	Quiet Series <sup>TM</sup>	TinyPower <sup>TM</sup>	
FRFET <sup>TM</sup>	MSX <sup>TM</sup>	RapidConfigure <sup>TM</sup>	TinyLogic <sup>®</sup>	
	MSXPro <sup>TM</sup>	RapidConnect <sup>TM</sup>	TINYOPTO <sup>TM</sup>	
Across the board. Around the world. <sup>TM</sup>		μSerDes <sup>TM</sup>	TruTranslation <sup>TM</sup>	
The Power Franchise <sup>®</sup>		ScalarPump <sup>TM</sup>	UHC <sup>TM</sup>	
Programmable Active Droop <sup>TM</sup>				

**DISCLAIMER**

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

**LIFE SUPPORT POLICY**

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in significant injury to the user.
- A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

**PRODUCT STATUS DEFINITIONS**

**Definition of Terms**

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.

Rev. I20